


**Form 1449 (Modified)**

**Information Disclosure  
Statement By Applicant**  
(Use Several Sheets if Necessary)

Atty Docket No.  
NOVLP033X1/NVLS-  
000498X1

Application No.:  
10/649,351

Applicant:  
Lee et al.  
Filing Date  
August 26, 2003

Group  
1762

**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
lhy	A1	6,551,929	04.2003	Kori et al.			
	A2	6,099,904	08.2000	Mak et al.			
	A3	5,227,329	07.1993	Kobayashi et al.			
	A4	6,017,818	01.2000	Lu, Jiong-Ping			
	A5	6,355,558	03.2002	Dixit et al.			
	A6	6,001,729	12.1999	Shinriki et al.			
	A7	6,844,258	01.18.05	Fair et al.			
	A8	6,174,812	01/16/01	Hsiung, et al.			
	A9	6,566,250	05/20/03	Tu, et al.			
	A10	6,566,262	05/20/03	Rissman, et al.			
	A11	6,706,625	03/16/04	Sudijono, et al.			
	A12	2004/0044127	03.04.04	Okubo et al.			
✓	A13	2004/0206267	10.21.04	Sambasivan et al.			

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
lhy	C1	U.S. Office Action mailed July 12, 2005, from U.S. Application No. 10/815,560 / [Atty Dkt. NOVLP096/NVLS-2902] ✓
lhy	C2	Wongsenakhum et al., "Method of Forming Low-Resistivity Tungsten Interconnects", Novellus Systems, Inc., filed March 31, 2004, Application No. 10/815,560, pages 1-30. [Atty Dkt. NOVLP096/NVLS-2902] ✓
lhy	C3	U.S. Office Action mailed July 17, 2002, from U.S. Application No. 09/975,074 / [Atty Dkt. NOVLP033/NVLS-000498]. ✓
lhy	C4	Presentation by Inventor James Fair: "Chemical Vapor Deposition of Refractory Metal Silicides," 27 Pages, 1983 ✓
lhy	C5	Saito et al., "A Novel Copper Interconnection Technology Using Self Aligned Metal Capping Method," IEEE, 3 Pages, 2001 ✓
lhy	C6	U.S. Office Action mailed June 22, 2004, from U.S. Application No. 10/435,010 / [Atty Dkt. NOVLP058/NVLS-000730]. ✓
lhy	C7	Levy et al., "Deposition of Tungsten Nitride", Novellus Systems, Inc., filed October 20, 2003, Application No. 10/690,492, pages 1-42. [Atty Dkt. NOVLP063/NVLS-000615] ✓
Examiner <i>lhy</i>		Date Considered <i>12-22-5</i>

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>Form 1449 (Modified)</b>	<b>Atty Docket No.</b> NOVLP033X1/NVLS- 000498X1	<b>Application No.:</b> 10/649,351
<b>Information Disclosure Statement By Applicant</b>	<b>Applicant:</b> Lee et al.	
(Use Several Sheets if Necessary)	<b>Filing Date</b> August 26, 2003	<b>Group</b> 1762

#### **Other Documents**

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



DEC 08 2005

<b>Form 1449 (Modified)</b> <b>Information Disclosure Statement By Applicant</b> <b>(Use Several Sheets if Necessary)</b>	<b>Atty Docket No.</b> <b>NOVLP033X1/NVLS- 000498X1</b> <b>Applicant:</b> <b>Lee et al.</b> <b>Filing Date</b> <b>August 26, 2003</b>	<b>Application No.:</b> <b>10/649,351</b> <b>Group</b> <b>1762</b>
---	--	---

## **U.S. Patent Documents**

### **Foreign Patent or Published Foreign Patent Application**

## **Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
lh	C1	U.S. Office Action mailed November 8, 2004, from U.S. Application No. 10/984,126 [Atty Dkt. NOVLP058D1/NVLS-000732D1]. ✓
lh	C2	Chan et al., "Methods for Growing Low-Resistivity Tungsten Film", Novellus Systems, Inc., filed November 1, 2005, Application No. 11/265,531, pages 1-35. [NOVLP137/NVLS-0003093] ✓
Examiner	lh	Date Considered 12-22-5

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.